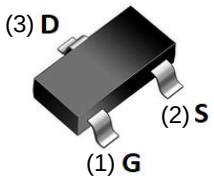
WG2301A

Features:

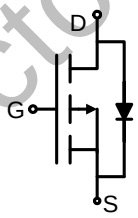
- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 2.9nC (Typ.)
- ☐ BVDSS=-20V,ID=-3A
- ☐ Rds(on) :55mΩ (Typ.) @V G=-4.5V
- ☐ 100% Avalanche Tested

SOT-23

RoHS COMPLIANT



1:Gate (G)
2:Source (S)
3:Drain (D)



Marking:A1SHB

Schematic diagram

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Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	-3	A
Drain Current -Pulsed (Note 1)	I_{DM}	-10	A
Maximum Power Dissipation	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-20	-24	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V,V_{GS}=0V	-	-	-1	μA
Parameter	**Symbol**	**Condition**	**Min**	**Typ**	**Max**	**Unit**
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-0.4	-0.62	-1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-3A	-	55	70	mΩ
		V_{GS}=-2.5V, I_D=-2A	-	70	100	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-2A	4	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	V_{DS}=-10V,V_{GS}=0V, F=1.0MHz	-	285	-	PF
Output Capacitance	C_{oss}		-	58	-	PF
Reverse Transfer Capacitance	C_{rss}		-	32	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-10V,I_D=-1A V_{GS}=-4.5V,R_{GEN}=3Ω	-	9.8	-	nS
Turn-on Rise Time	t_r		-	4.9	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	20.5	-	nS
Turn-Off Fall Time	t_f		-	7	-	nS
Total Gate Charge	Q_g	V_{DS}=-10V,I_D=-3A, V_{GS}=-4.5V	-	2.9	-	nC
Gate-Source Charge	Q_{gs}		-	0.45	-	nC
Gate-Drain Charge	Q_{gd}		-	0.75	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-3A	-	-	-1.2	V
Diode Forward Current (Note2)	I_S		-	-	-3	A

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Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Characteristics

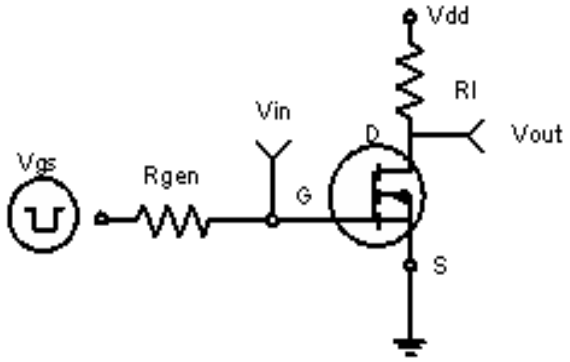


Figure 1:Switching Test Circuit

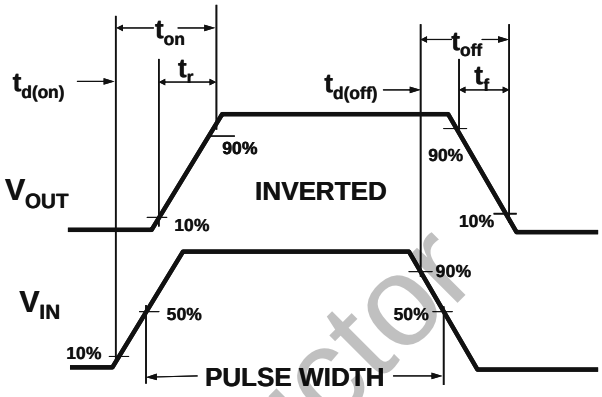


Figure 2:Switching Waveforms

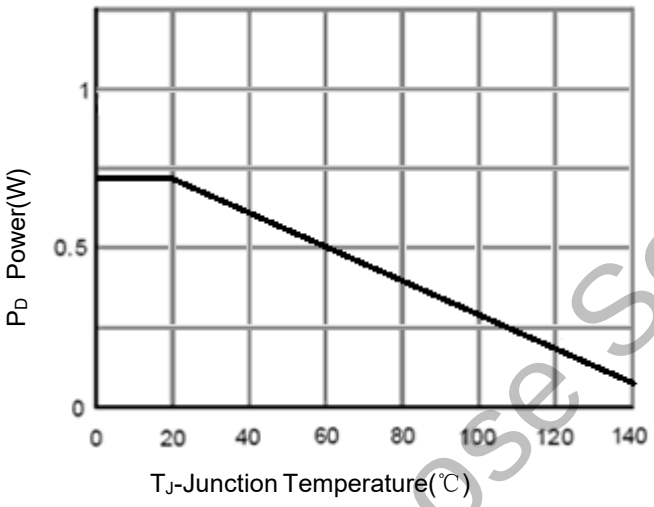


Figure 3 Power Dissipation

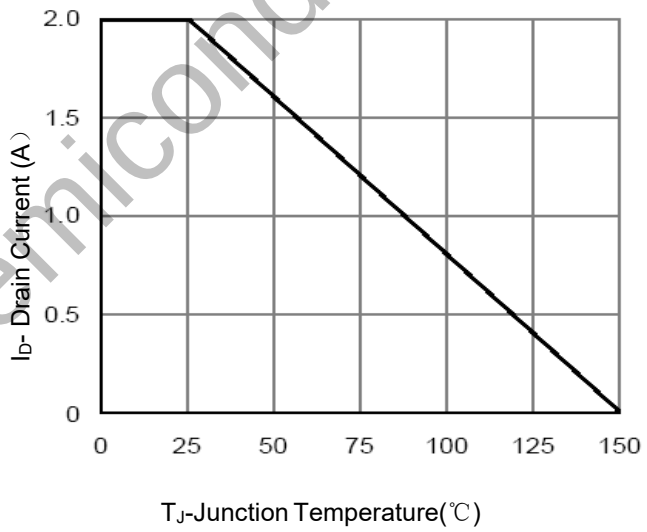


Figure 4 Drain Current

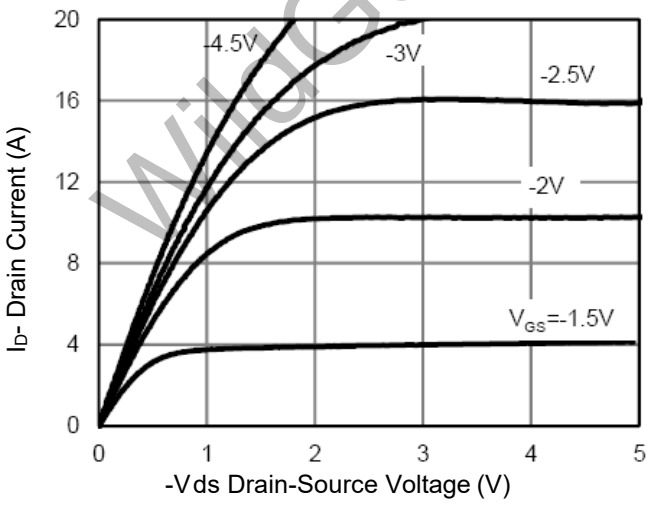


Figure 5 Output Characteristics

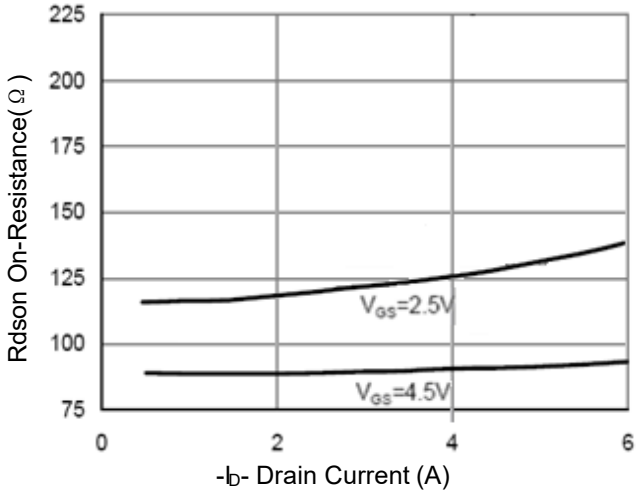


Figure 6 Drain-Source On-Resistance

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Typical Characteristics (Continued)

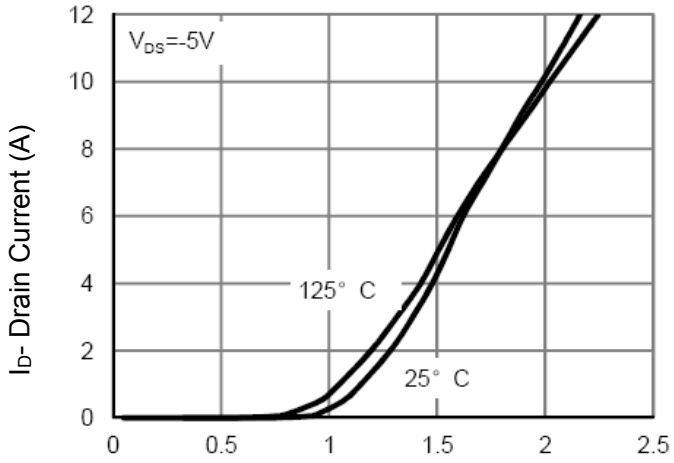


Figure 7 Transfer Characteristics

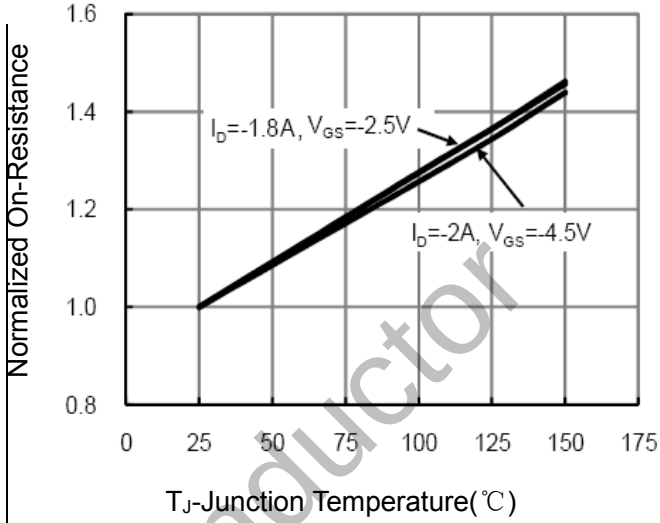


Figure 8 Drain-Source On-Resistance

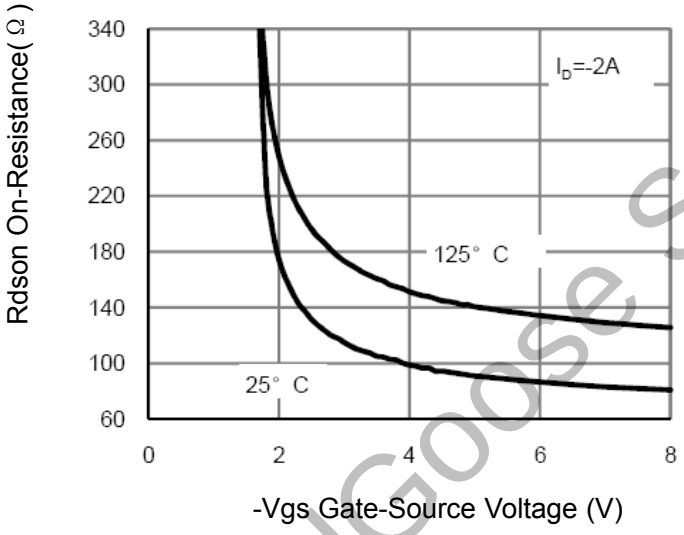


Figure 9 Rdson vs Vgs

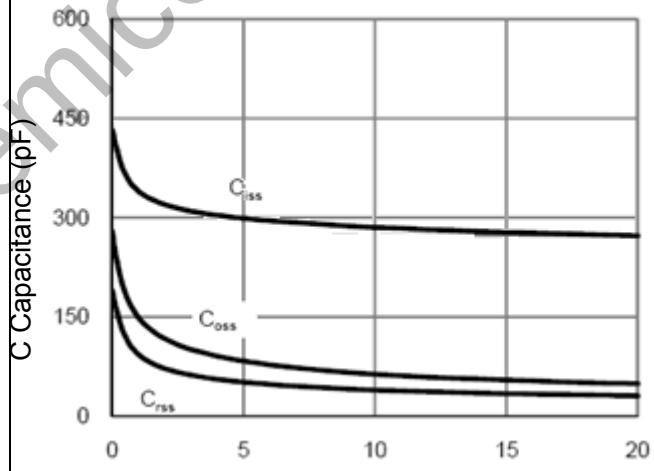


Figure 10 Capacitance vs Vds

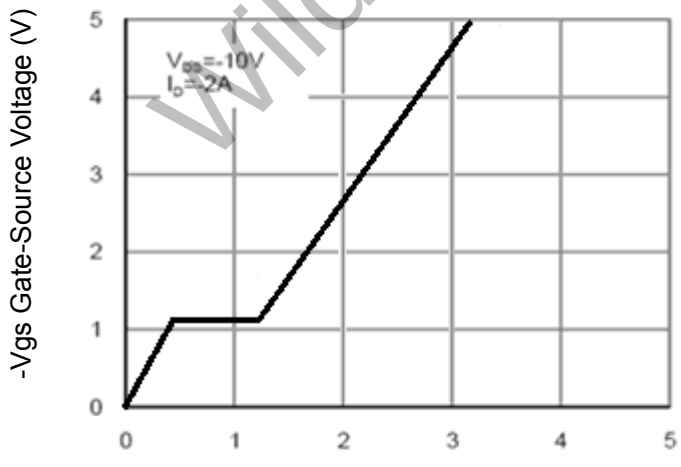


Figure 11 Gate Charge

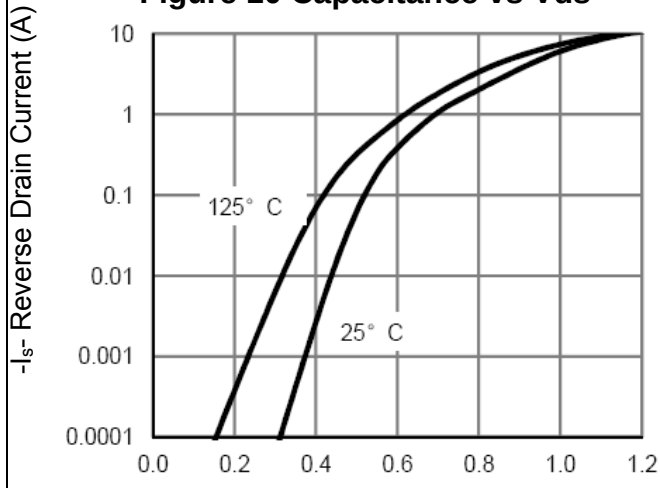


Figure 12 Source- Drain Diode Forward

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Typical Characteristics (Continued)

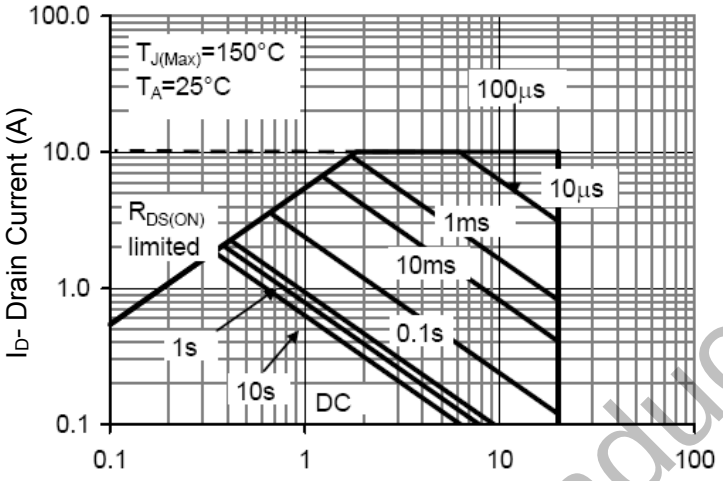


Figure 13 Safe Operation Area

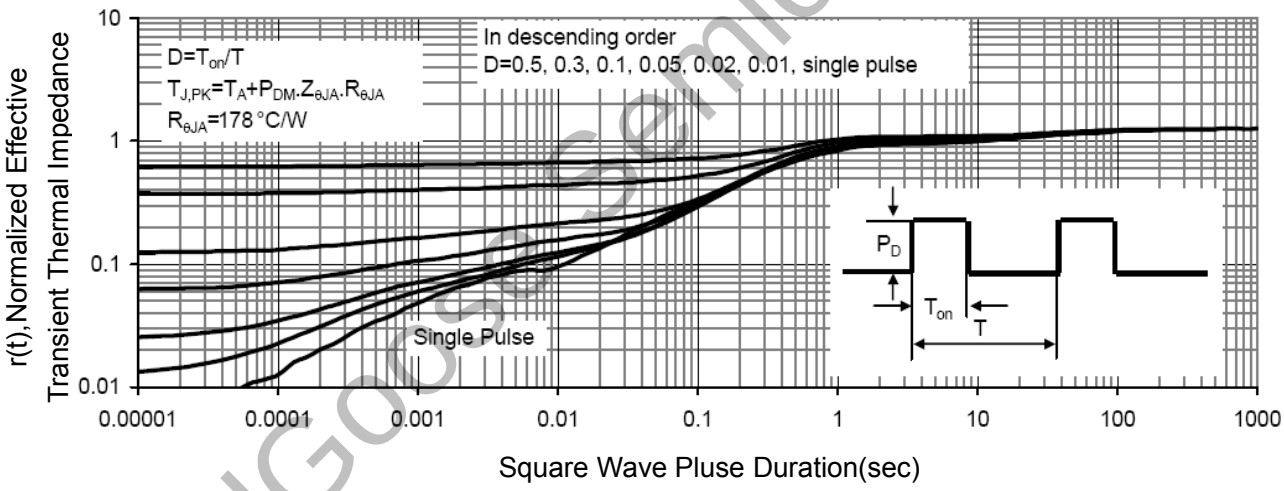


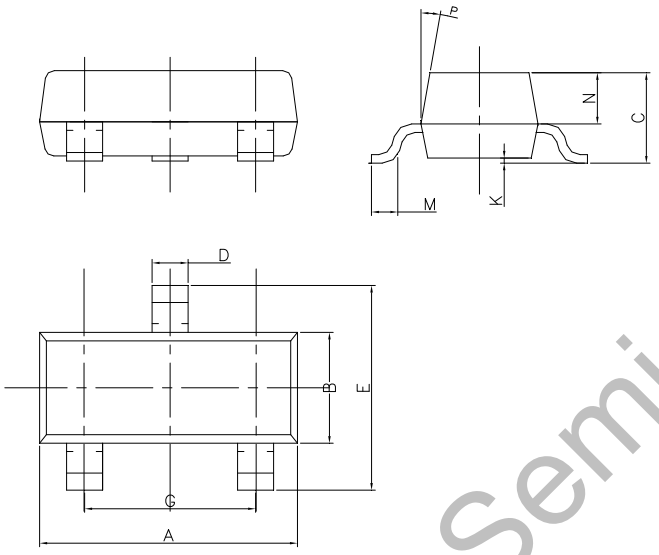
Figure 14 Normalized Maximum Transient Thermal Impedance

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Package Dimension

SOT-23

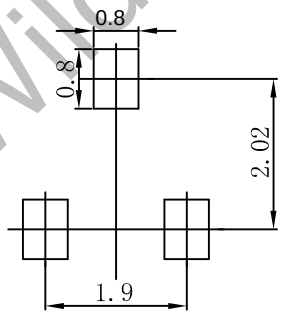
Unit: mm



DIM	MILLIMETERS
A	2.85~3.04
B	1.30±0.10
C	1.00±0.10
D	0.45±0.05
E	2.25~2.55
G	1.90±0.1
K	0.00−0.10
M	0.20 MIN
N	0.60±0.10
P	7±2°

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SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.